















**ESD** 

TVS

MOS

LDO

Diode

Sensor

DC-DC

# **Product Specification**

Domestic Part Number	MJL1302A
Overseas Part Number	MJL1302A
▶ Equivalent Part Number	MJL1302A





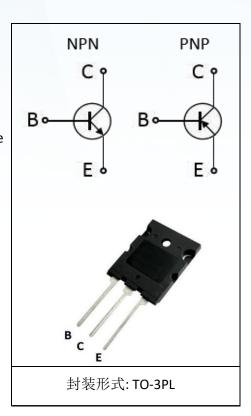
### **Minos Silicon PNP Epitaxial Type**

#### **MJL1302A**

#### **Power Amplifier Applications**

- ① Complementary to MJL3281A
- 2 High collector voltage:V<sub>CEO</sub>=-260V(min)
- 3 Recommended for 100-W high-fidelity audio frequency amplifier Output stage

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



## Absolute Maximum Ratings(Tc=25 $^{\circ}$ C):

Symbol	Parameter	Value	Units
VcBO	Collector-base voltage	-260	V
VCEO	Collector-emitter voltage	-260	V
VEBO	Emitter-base voltage	-5	V
Ic	Collector current	-15	А
I <sub>B</sub>	Base current	-5	А
Pc	Collector power dissipation (Tc=25 $^{\circ}\mathrm{C}$ )	200	W
Tj	Junction temperature	150	$^{\circ}$
Тѕтс	Storage temperature range	-55~150	$^{\circ}$

#### **Thermal Characteristics**

Symbol	Parameter	Тур	Units
$R_{\theta JC}$	Junction-to-Case	0.63	°C/W

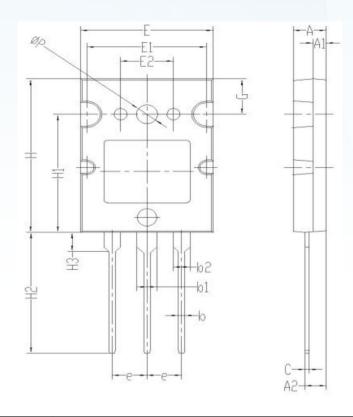


# Electrical Characteristics (Tc=25°C)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Ісво	Collector cut-off current	V <sub>CB</sub> =-250V; I <sub>E</sub> =0			-50.0	uA
<b>І</b> ЕВО	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>c</sub> =0			-50.0	uA
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA;I <sub>B</sub> =0	-260			٧
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> =-5V; I <sub>C</sub> =-8A;	20		80	
h <sub>FE(2)</sub>		V <sub>CE</sub> =-5V; I <sub>C</sub> =-15A;	8			
Vce(sat)	Collector-emitter saturation voltage	Ic=-8A; I <sub>B</sub> =-0.8A			-1.4	٧
Vce(sat)		Ic=-15A; I <sub>B</sub> =-3.2A			-4	٧
V <sub>BE</sub>	Base-emitter voltage	V <sub>CE</sub> =-5V;I <sub>C</sub> =-8A			-2.2	٧
f⊤	Transition frequency	V <sub>CE</sub> =-10V; I <sub>C</sub> =-1A	4			MHz



# **Package Description**



Cumbal	Values(mm)		
Symbol	Min.	Max.	
Α	4.80	5.20	
A1	1.80	2.20	
A2	3.00	3.40	
b	0.80	1.20	
b1	2.80	3.20	
b2	2.30	2.70	
С	0.40	0.80	
e	5.25	5.65	
Е	19.80	20.20	
E1	17.80	18.20	
E2	7.80	8.20	
Н	25.80	26.20	
H1	19.80	20.20	
H2	20.00	21.00	
Н3	3.05	3.45	
G	5.80	6.20	
ФР	3.10	3.50	
J	4.80	5.20	
К	1.80	2.20	

**TO-3PL Package** 



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